

Amendments to the Claims

The following listing of claims replaces any previous versions and listings of claims in the application.

Listing of Claims:

1. (currently amended) A method for manufacturing a semiconductor device with capacitor elements, comprising:

forming a conductive layer on a first insulating layer formed on a substrate, and on a plurality of contact plugs formed in the first insulating layer;

forming a plurality of capacitor element lower electrodes by patterning the conductive layer;

forming a second insulating layer on the first insulating layer and the capacitor element lower electrodes;

forming a recess in the second insulating layer, the recess being positioned at a region above at least one of the capacitor element lower electrodes, without exposing a surface of the at least one capacitor element lower electrode over which the recess is positioned electrodes;

planarizing the second insulating layer with the recess by polishing so as to not expose the surface of the capacitor element lower electrodes;

exposing the capacitor element lower electrodes by removing a surface portion of the planarized second insulating layer; and

forming a capacitive insulating film and capacitor element upper electrodes above the capacitor element lower electrodes.

2. (original) The method for manufacturing a semiconductor device according to claim 1, wherein the step of exposing the capacitor element lower electrodes is carried out by etchback.

3. (original) The method for manufacturing a semiconductor device according to claim 2, wherein the step of planarizing the second insulating layer by polishing is carried out by CMP (chemical mechanical polishing).

4-7. (canceled)

8. (previously presented) The method for manufacturing a semiconductor device according to claim 1, wherein a surface of the conductive layer is made of Pt, Ir, Ru, an alloy thereof or a metal oxide thereof.

9. (original) The method for manufacturing a semiconductor device according to claim 1, wherein the step of forming a recess in the second insulating layer is performed by dry etching.

10-12. (canceled)

13. (original) The method for manufacturing a semiconductor device according to claim 1, wherein the second insulating film is an SiO₂ film formed by atmospheric CVD using ozone and tetraethylorthosilicate.

14-17. (canceled)